

Abstract Submitted
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Topological Material-Based Spin Devices MINHAO ZHANG, XUE-FENG WANG, Nanjing Univ — Three-dimensional topological insulators have insulating bulk and gapless helical surface states. One of the most fascinating properties of the metallic surface states is the spin-momentum helical locking. The giant current-driven torques on the magnetic layer have been discovered in TI/ferromagnet bilayers originating from the spin-momentum helical locking, enabling the efficient magnetization switching with a low current density.¹ We demonstrated the current-direction dependent on-off state in TIs-based spin valve devices for memory and logic applications.² Further, we demonstrated the Bi_2Se_3 system will go from a topologically nontrivial state to a topologically trivial state when Bi atoms are replaced by lighter In atoms. Here, topologically trivial metal $(\text{Bi}_x\text{In}_y)_2\text{Se}_3$ with high mobility also facilitates the realization of its application in multifunctional spintronic devices.
¹A. Mellnik, et al, Nature **511** (7510), 449 (2014). ²M. Zhang, et al, IEEE Electron Device Letters **37** (9), 1231 (2016).

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